

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild guestions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer

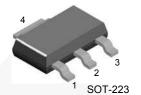


November 2014

NZT651 NPN Current Driver Transistor

Description

This device is designed for power amplifier, regulator and switching circuits where speed is important. Sourced from process 4P.



1. Base 2,4. Collector 3. Emitter

Ordering Information

| Part Number | Marking | Package | Packing Method | |
|-------------|---------|------------|----------------|--|
| NZT651 | 651 | SOT-223 4L | Tape and Reel | |

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

| Symbol | Parameter | Value | Unit |
|-----------------------------------|--|-------------|------|
| V _{CEO} | Collector-Emitter Voltage | 60 | V |
| V _{CBO} | Collector-Base Voltage | 80 | V |
| V_{EBO} | Emitter-Base Voltage | 5.0 | V |
| I _C | Collector Current - Continuous | 4.0 | Α |
| T _J , T _{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics(3)

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | Max. | Unit |
|-----------------|---|------|-------|
| P _D | Total Power Dissipation | 1.2 | W |
| | Derate Above 25°C | 9.7 | mW/°C |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | 103 | °C/W |

Note:

3. Device is mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead minimum 6 cm².

Electrical Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | Conditions | Min. | Max. | Unit |
|-----------------------|--|---|------|------|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 10 mA, I _B = 0 | 60 | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | $I_C = 100 \mu A, I_E = 0$ | 80 | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 100 μA, I _C = 0 | 5.0 | | V |
| I _{CBO} | Collector Cut-Off Current | $V_{CB} = 80 \text{ V}, I_{E} = 0$ | | 100 | nA |
| I _{EBO} | Emitter Cut-Off Current | $V_{EB} = 4.0 \text{ V}, I_{C} = 0$ | | 0.1 | μΑ |
| | | I_C = 50 mA, V_{CE} = 2.0 V | 75 | | |
| h _{FE} | DC Current Gain ⁽⁴⁾ | I_C = 500 mA, V_{CE} = 2.0 V | 75 | | |
| | | I _C = 1.0 A, V _{CE} = 2.0 V | 75 | | |
| | | I _C = 2.0 A, V _{CE} = 2.0 V | 40 | | |
| V _{CE} (sat) | Collector-Emitter Saturation | I _C = 1.0 A, I _B = 100 mA | | 0.3 | |
| | Voltage ⁽⁴⁾ | $I_C = 2.0 \text{ A}, I_B = 200 \text{ mA}$ | | 0.5 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage ⁽⁴⁾ | I _C = 1.0 A, I _B = 100 mA | | 1.2 | V |
| V _{BE} (on) | Base-Emitter On Voltage ⁽⁴⁾ | I _C = 1.0 A, V _{CE} = 2.0 V | | 1.0 | V |
| f _T | Current Gain - Bandwidth Product | I _C = 50 mA, V _{CE} = 5.0 V, f = 100 MHz | 75 | | MHz |

Note:

4. Pulse test: pulse width ≤ 300 μs, duty cycle ≤ 2.0%

Typical Performance Characteristics

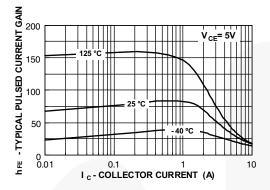


Figure 1. Typical Pulsed Current Gain vs. Collector Current

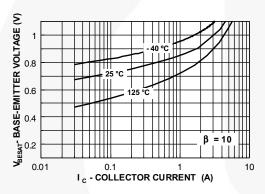


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

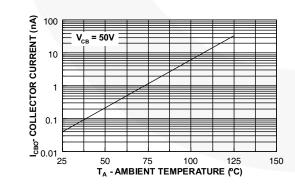


Figure 5. Collector Cut-Off Current vs.
Ambient Temperature

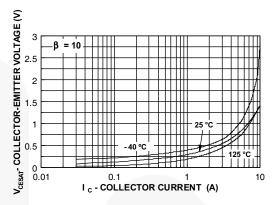


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

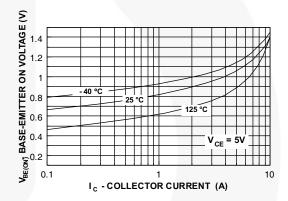


Figure 4. Base-Emitter On Voltage vs. Collector Current

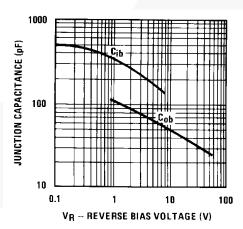


Figure 6. Junction Capacitance vs. Reverse Bias Voltage

Typical Performance Characteristics (Continued)

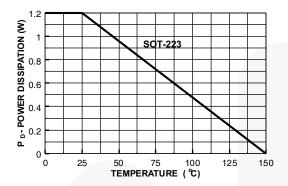
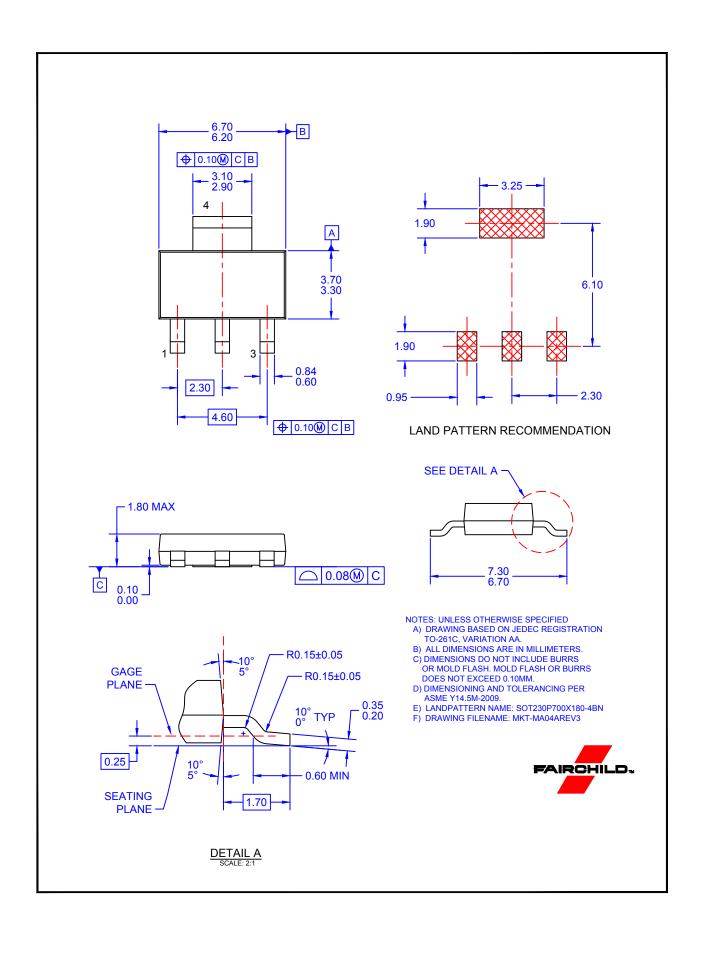


Figure 7. Power Dissipation vs. Ambient Temperature



ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hol

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative